

# FCH20N60 / FCA20N60 600V N-Channel MOSFET

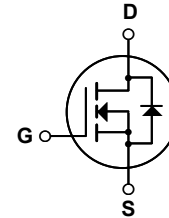
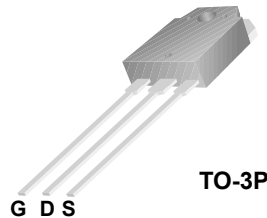
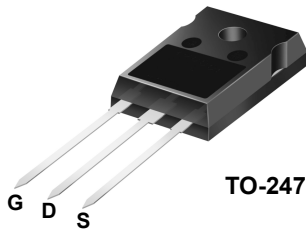
## Features

- 650V @ $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 0.15\Omega$
- Ultra low gate charge (typ.  $Q_g = 75\text{nC}$ )
- Low effective output capacitance (typ.  $C_{oss-eff} = 165\text{pF}$ )
- 100% avalanche tested

## Description

SuperFET™ is, Fairchild's proprietary, new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme  $dv/dt$  rate and higher avalanche energy. Consequently, SuperFET is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.



## Absolute Maximum Ratings

Symbol	Parameter	FCH20N60	FCA20N60	Unit
$V_{DSS}$	Drain-Source Voltage	600		V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	20 12.5		A A
$I_{DM}$	Drain Current - Pulsed (Note 1)	60		A
$V_{GSS}$	Gate-Source voltage	$\pm 30$		V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	690		mJ
$I_{AR}$	Avalanche Current (Note 1)	20		A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	20.8		mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ (Note 3)	4.5		V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	208 1.67		W W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

## Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.6	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	41.7	$^\circ\text{C}/\text{W}$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCH20N60	FCH20N60	TO-247	-	-	30
FCA20N60	FCA20N60	TO-3P	-	-	30

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

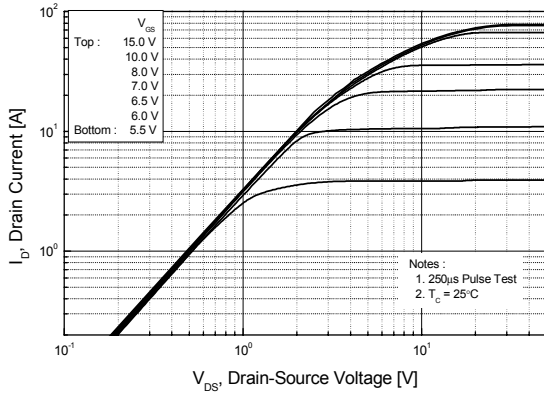
Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A, T_J = 25^\circ\text{C}$	600	--	--	V
		$V_{GS} = 0V, I_D = 250\mu A, T_J = 150^\circ\text{C}$	--	650	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$ , Referenced to $25^\circ\text{C}$	--	0.6	--	$V/^\circ\text{C}$
$BV_{DS}$	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0V, I_D = 20A$	--	700	--	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	--	--	1	$\mu A$
		$V_{DS} = 480V, T_C = 125^\circ\text{C}$	--	--	10	$\mu A$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30V, V_{DS} = 0V$	--	--	-100	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 10A$	--	0.15	0.19	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40V, I_D = 10A$ (Note 4)	--	17	--	S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{MHz}$	--	2370	3080	pF
$C_{oss}$	Output Capacitance		--	1280	1665	pF
$C_{riss}$	Reverse Transfer Capacitance		--	95	--	pF
$C_{oss}$	Output Capacitance	$V_{DS} = 480V, V_{GS} = 0V, f = 1.0\text{MHz}$	--	65	85	pF
$C_{oss \text{ eff.}}$	Effective Output Capacitance	$V_{DS} = 0V \text{ to } 400V, V_{GS} = 0V$	--	165	--	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300V, I_D = 20A, R_G = 25\Omega$	--	62	135	ns
$t_r$	Turn-On Rise Time		--	140	290	ns
$t_{d(off)}$	Turn-Off Delay Time		--	230	470	ns
$t_f$	Turn-Off Fall Time		(Note 4, 5)	--	65	140
$Q_g$	Total Gate Charge	$V_{DS} = 480V, I_D = 20A, V_{GS} = 10V$	--	75	98	nC
$Q_{gs}$	Gate-Source Charge		--	13.5	18	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4, 5)	--	36	--
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current		--	--	20	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current		--	--	60	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 20A$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0V, I_S = 20A, di_f/dt = 100A/\mu s$	--	530	--	ns
$Q_{rr}$	Reverse Recovery Charge		(Note 4)	--	10.5	--

### Notes:

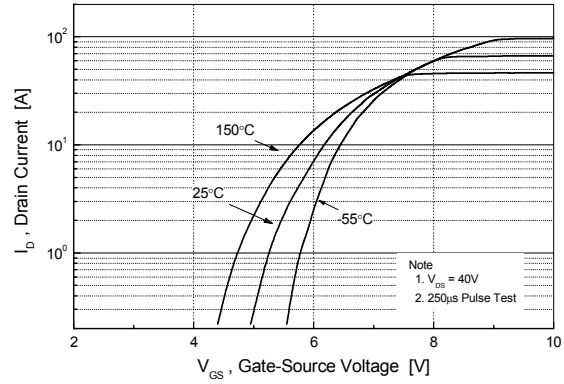
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS} = 10A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 20A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

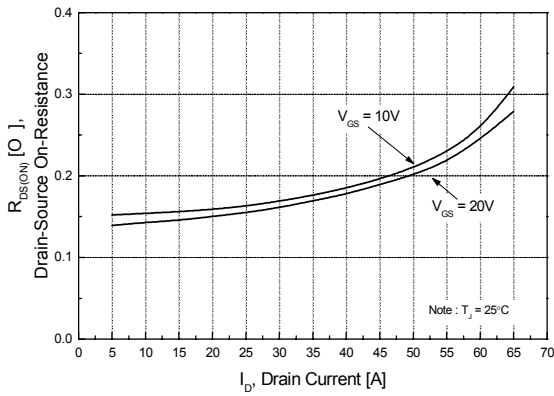
**Figure 1. On-Region Characteristics**



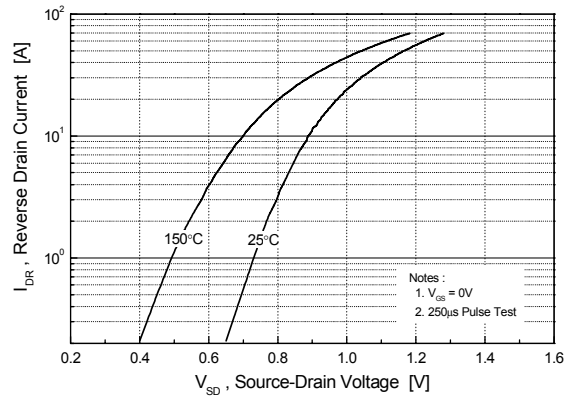
**Figure 2. Transfer Characteristics**



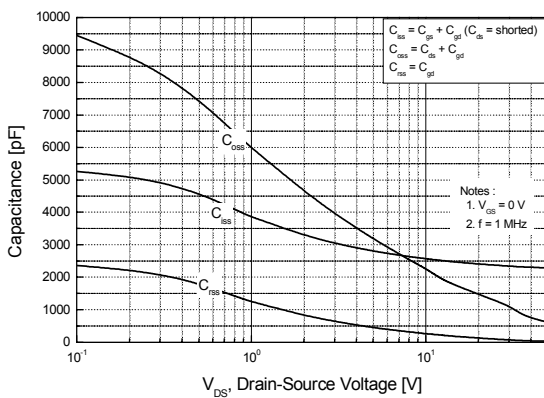
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



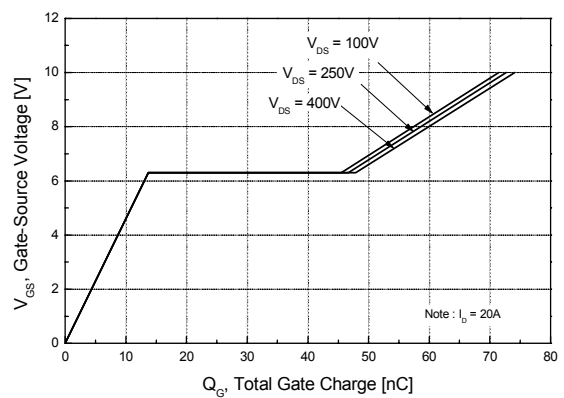
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

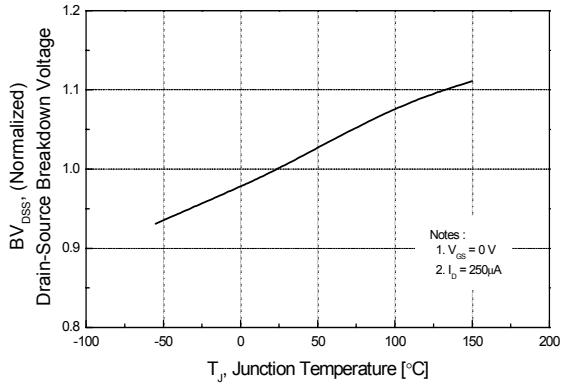


**Figure 6. Gate Charge Characteristics**

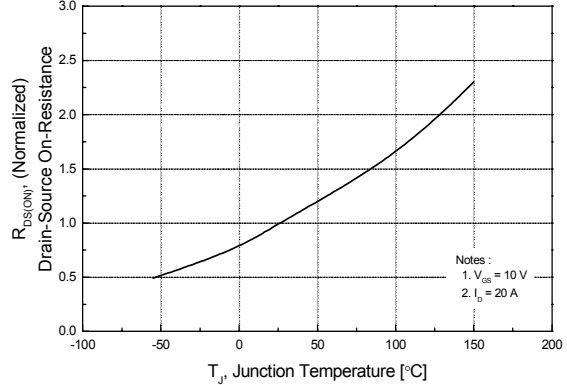


**Typical Performance Characteristics** (Continued)

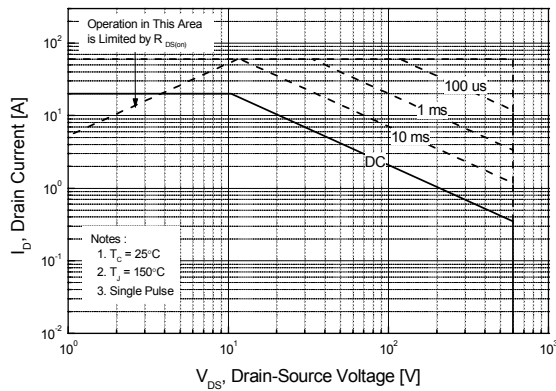
**Figure 7. Breakdown Voltage Variation vs. Temperature**



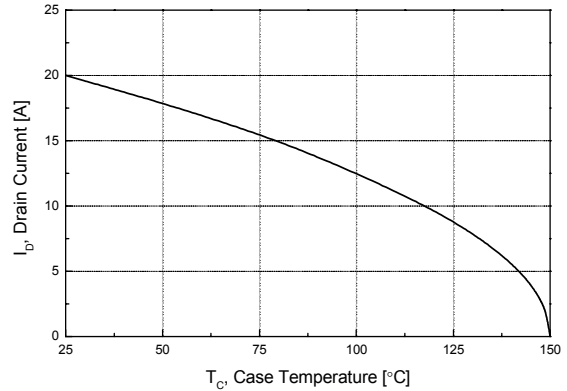
**Figure 8. On-Resistance Variation vs. Temperature**



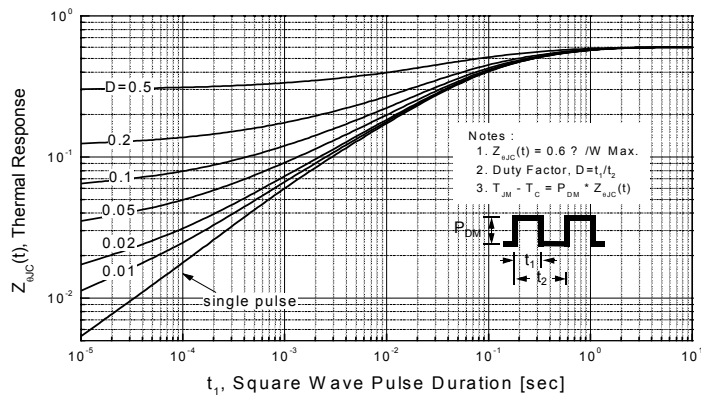
**Figure 9. Maximum Safe Operating Area**



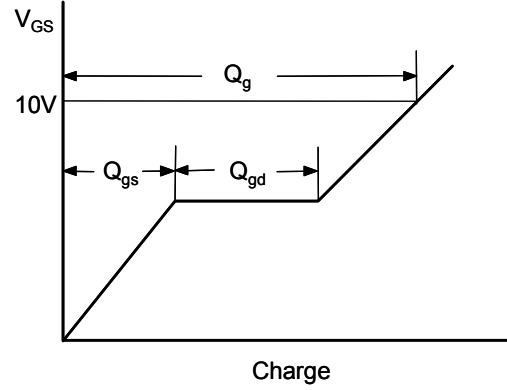
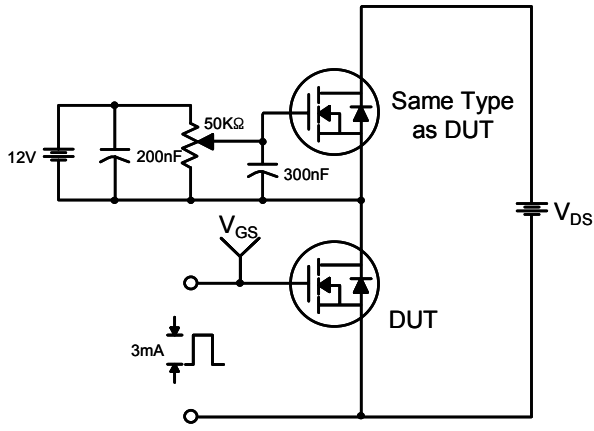
**Figure 10. Maximum Drain Current vs. Case Temperature**



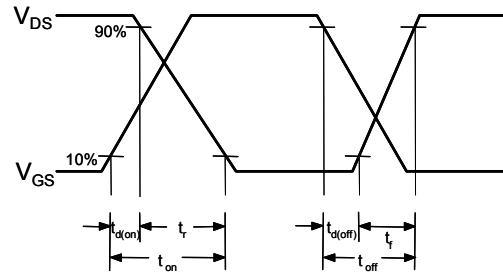
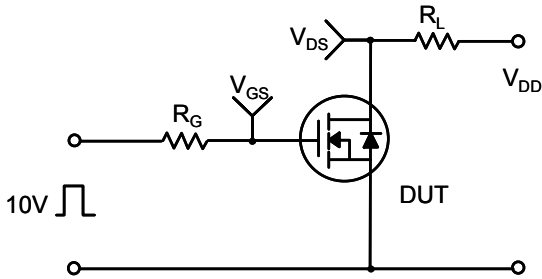
**Figure 11. Transient Thermal Response Curve**



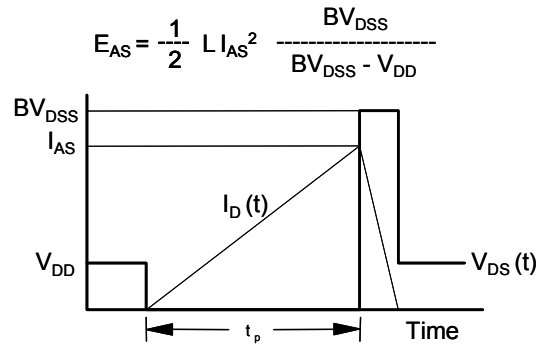
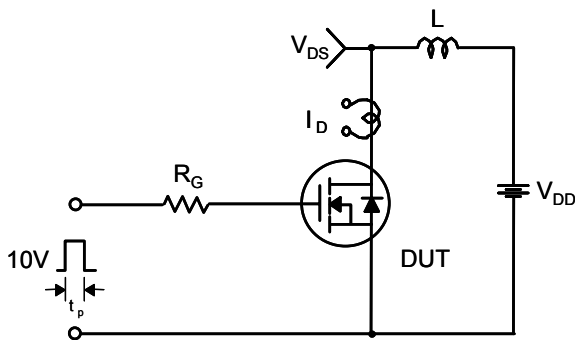
**Gate Charge Test Circuit & Waveform**



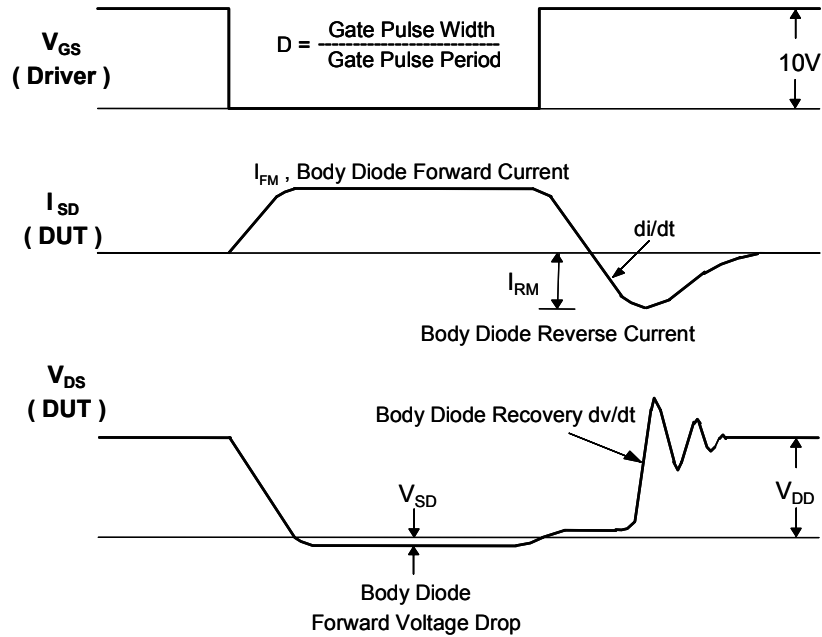
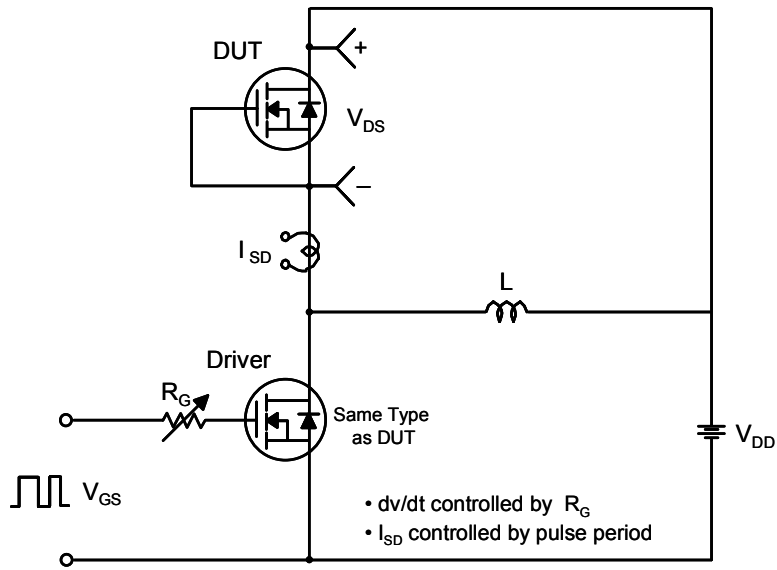
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**



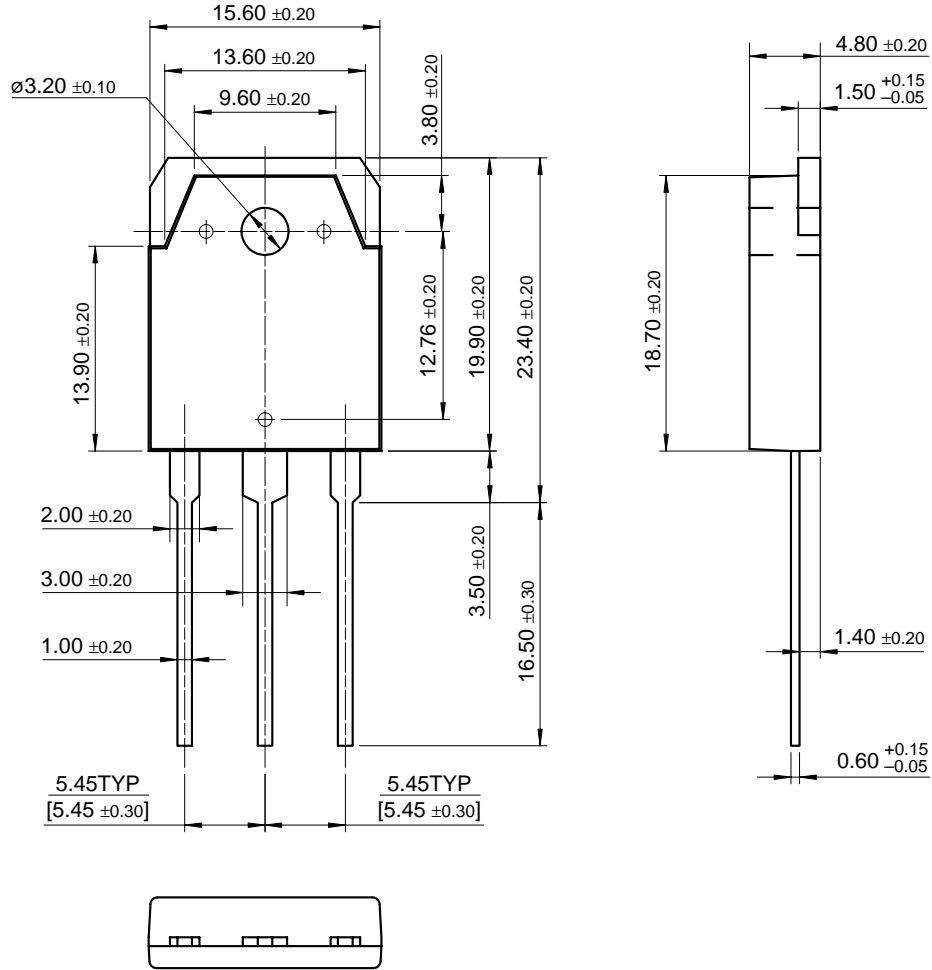
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions (Continued)

TO-3P



Dimensions in Millimeters



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EcoSPARK™	I <sup>2</sup> C™	MSXPro™	RapidConnect™	UniFET™
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FACT™	IntelliMAX™	OPTOLOGIC®	SMART START™	
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The Power Franchise®		POP™	SuperFET™	
Programmable Active Droop™		Power247™	SuperSOT™-3	
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## PRODUCT STATUS DEFINITIONS

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